64K (8K x 8)

**CMOS** 

E<sup>2</sup>PROM

#### 2

#### **Features**

- Fast Read Access Time 120 ns
- Fast Byte Write 200 μs or 1 ms
- Self-Timed Byte Write Cycle Internal Address and Data Latches Internal Control Timer Automatic Clear Before Write
- Direct Microprocessor Control
   READY/BUSY Open Drain Output
   DATA Polling
- Low Power
   30 mA Active Current
   100 µA CMOS Standby Current
- High Reliability
   Endurance: 10<sup>4</sup> or 10<sup>5</sup> Cycles
   Data Retention: 10 years
- 5 V ± 10% Supply
- CMOS and TTL Compatible Inputs and Outputs
- JEDEC Approved Byte-Wide Pinout
- Full Military, Commercial, and Industrial Temperature Ranges

### Description

The AT28C64 is a low-power, high-performance 8,192 words x 8 bit nonvolatile Electrically Erasable and Programmable Read Only Memory with popular, easy to use features. The device is manufactured with Atmel's reliable nonvolatile technology.

The AT28C64 is accessed like a Static RAM for the read or write cycles without the need for external components. During a byte write, the address and data are latched internally, freeing the microprocessor address and data bus for other operations. Following the initiation of a

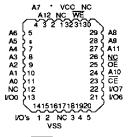
(continued on next page)

## **Pin Configurations**

				1001 TOP VIEW				
A11 A8 WE ROY/BUSY A7 A5	OE	1 2	1 3 5 7 9 11	TSGF TOP VIEW	28 26 24 22 20 18 16	27 25 23 21 19	A10 VO7 VO5 VO3 VO2 VO2 A1	CE I/O6 I/O4 GND I/O1 A0
A3	<u> </u>	14	13			15	י^ כַּ	A2

TSOP Too View

Pin Name	Function
A0 - A12	Addresses
CE	Chip Enable
ŌĒ	Output Enable
WE	Write Enable
1/00 - 1/07	Data Inputs/Outputs
RDY/BUSY	Ready/Busy Output
NC	No Connect



· = RDY/BUSY (or NC)

Note: PLCC package pins 1 and 17 are DON'T CONNECT.



2-91

1074177 0005038 121 1



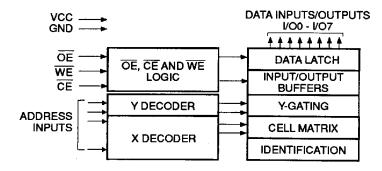
### **Description** (Continued)

write cycle, the device will go to a busy state and automatically clear and write the latched data using an internal control timer. The device includes two methods for detecting the end of a write cycle, level detection of RDY/BUSY (unless pin 1 is N.C.) and DATA polling of I/O7. Once the end of a write cycle has been detected, a new access for a read or write can begin.

The CMOS technology offers fast access times of 150 ns at low power dissipation. When the chip is deselected the standby current is less than  $100 \, \mu A$ .

Atmel's 28C64 has additional features to ensure high quality and manufacturability. The device utilizes error correction internally for extended endurance and for improved data retention characteristics. An extra 32 bytes of E<sup>2</sup>PROM are available for device identification or tracking.

#### **Block Diagram**



## **Absolute Maximum Ratings\***

Temperature Under Bias55°C to +125°C
Storage Temperature65°C to +150°C
All Input Voltages (including N.C. Pins) with Respect to Ground0.6 V to +6.25 V
All Output Voltages with Respect to Ground0.6 V to Vcc +0.6 V
Voltage on OE and A9 with Respect to Ground0.6 V to +13.5 V

\*NOTICE: Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

AT28C64/X

2-92

1074177 0005039 068 ■

### **Device Operation**

READ: The AT28C64 is accessed like a Static RAM. When  $\overline{CE}$  and  $\overline{OE}$  are low and  $\overline{WE}$  is high, the data stored at the memory location determined by the address pins is asserted on the outputs. The outputs are put in a high impedance state whenever  $\overline{CE}$  or  $\overline{OE}$  is high. This dual line control gives designers increased flexibility in preventing bus contention.

BYTE WRITE: Writing data into the AT28C64 is similar to writing into a Static RAM. A low pulse on the  $\overline{WE}$  or  $\overline{CE}$  input with  $\overline{OE}$  high and  $\overline{CE}$  or  $\overline{WE}$  low (respectively) initiates a byte write. The address location is latched on the falling edge of  $\overline{WE}$  (or  $\overline{CE}$ ); the new data is latched on the rising edge. Internally, the device performs a self-clear before write. Once a byte write has been started, it will automatically time itself to completion.

FAST BYTE WRITE: The AT28C64F offers a byte write time of 200 µs maximum. This feature allows the entire device to be rewritten in 1.6 seconds.

READY/BUSY: Pin 1 is an open drain READY/BUSY output that can be used to detect the end of a write cycle. RDY/BUSY is actively pulled low during the write cycle and is released at the completion of the write. The open drain connection allows for OR-tying of several devices to the same RDY/BUSY line. Pin 1 is not connected for the AT28C64X.

DATA POLLING: The AT28C64 provides DATA POLLING to signal the completion of a write cycle. During a write cycle, an attempted read of the data being written results in the complement of that data for I/O7 (the other outputs are indeterminate). When the write cycle is finished, true data appears on all outputs.

WRITE PROTECTION: Inadvertent writes to the device are protected against in the following ways. (a) Vcc sense— if Vcc is below 3.8 V (typical) the write function is inhibited. (b) Vcc power on delay—once Vcc has reached 3.8 V the device will automatically time out 5 ms (typical) before allowing a byte write. (c) Write Inhibit—holding any one of  $\overline{OE}$  low,  $\overline{CE}$  high or  $\overline{WE}$  high inhibits byte write cycles.

CHIP CLEAR: The contents of the entire memory of the AT28C64 may be set to the high state by the CHIP CLEAR operation. By setting  $\overline{CE}$  low and  $\overline{OE}$  to 12 volts, the chip is cleared when a 10 msec low pulse is applied to  $\overline{WE}$ .

DEVICE IDENTIFICATION: An extra 32 bytes of  $E^2$ PROM memory are available to the user for device identification. By raising A9 to  $12 \pm 0.5$  V and using address locations 1FE0H to 1FFFH the additional bytes may be written to or read from in the same manner as the regular memory array.

## **Pin Capacitance** $(f = 1 \text{ MHz}, T = 25^{\circ}\text{C})^{(1)}$

	Тур	Max	Units	Conditions
CIN	4	6	pF	VIN = 0 V
Соит	8	12	pF	Vout = 0 V

Note: 1. This parameter is characterized and is not 100% tested.



2-93

**--** 1074177 0005040 88T



# D.C. and A.C. Operating Range

		AT28C64-12	AT28C64-15	AT28C64-20	AT28C64-25
0	Com.	0°C - 70°C	0°C - 70°C	0°C - 70°C	0°C - 70°C
Operating Temperature (Case)	ind.	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C	-40°C - 85°C
, ,	Mil.	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C	-55°C - 125°C
Vcc Power Supply		5 V ± 10%			

# **Operating Modes**

CE	ŌĒ	WE	I/O
VíL	VIL	ViH	Dout
VIL	ViH	VIL	DiN
ViH	X <sup>(1)</sup>	Х	High Z
Х	Х	ViH	
X	VIL	X	
Х	ViH	X	High Z
VIL	VH <sup>(3)</sup>	VIL	High Z
	VIL VIH X X X	VIL         VIL           VIL         VIH           VIH         X(1)           X         X           X         VIL           X         VIH	VIL         VIL         VIH           VIL         VIH         VIL           VIH         X         X           X         X         VIH           X         VIL         X           X         VIH         X

Notes: 1. X can be VIL or VIH.

2. Refer to A.C. Programming Waveforms.

#### 3. $V_H = 12.0 \text{ V} \pm 0.5 \text{ V}$ .

## **D.C. Characteristics**

Symbol	Parameter	Condition	<u> </u>	Min	Max	Units
Li	Input Load Current	VIN = 0 V to Vcc + 1 V			10	μΑ
Iro	Output Leakage Current	V <sub>I/O</sub> = 0 V to V <sub>CC</sub>			10	μА
ISB1	Vcc Standby Current CMOS	CE = Vcc-0.3 V to Vcc + 1.0 V			100	μА
ISB2 Vcc Standby Current TTL		CE = 2.0 V to Vcc + 1.0 V	Com.		2	mA
		CE = 2:0 V to VCC + 1:0 V	Ind., Mit.		3	mA
lcc	Vcc Active Current A.C.	f = 5 MHz; lout = 0 mA	Com.		30	mA
vcc Active Current A.C.		CE = VIL	Ind., Mil.		45	mA
VIL	Input Low Voltage				0.8	V
VIH	Input High Voltage			2.0		V
Vol	Output Low Voltage	IoL = 2.1 mA = 4.0 mA for RDY/BUSY			.45	٧
Vон	Output High Voltage	IOH = -400 μA		2.4	·	V

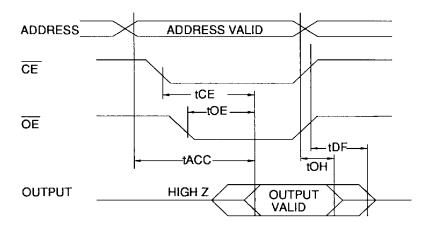
2-94 AT28C64/X =

1074177 0005041 716 📟

#### A.C. Read Characteristics

		AT28C64-12		AT28C64-15		AT28C64-20		AT28C64-25			
Symbol	Parameter	Min	Max	Min	Max	Min	Max	Min	Max	Units	
tacc	Address to Output Delay		120		150		200		250	ns	
tce (1)	CE to Output Delay		120		150		200		250	ns	
toE (2)	OE to Output Delay	10	60	10	70	10	80	10	100	ns	
tor (3,4)	CE or OE High to Output Float	0	45	0	50	0	55	0	60	ns	
tон	Output Hold from OE, CE or Address, whichever occurred first	0		0		0		0		ns	

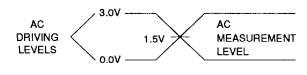
#### A.C. Read Waveforms



#### Notes

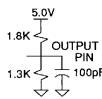
- CE may be delayed up to tACC tCE after the address transition without impact on tACC.
- OE may be delayed up to t<sub>CE</sub> t<sub>OE</sub> after the falling edge of CE without impact on t<sub>CE</sub> or by t<sub>ACC</sub> - t<sub>OE</sub> after an address change without impact on t<sub>ACC</sub>.
- 3.  $t_{DF}$  is specified from  $\overline{OE}$  or  $\overline{CE}$  whichever occurs first (C  $_L=5$  pF).
- 4. This parameter is characterized and is not 100% tested.

# Input Test Waveforms and Measurement Level



 $t_R$ ,  $t_F < 20$  ns

## **Output Test Load**





2-95

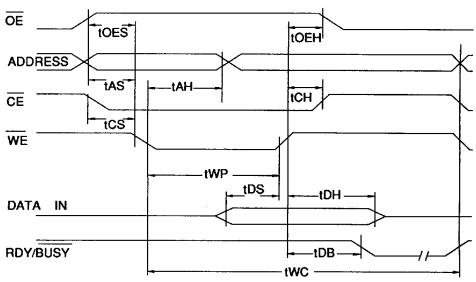
🖿 1074177 0005042 652 🖛



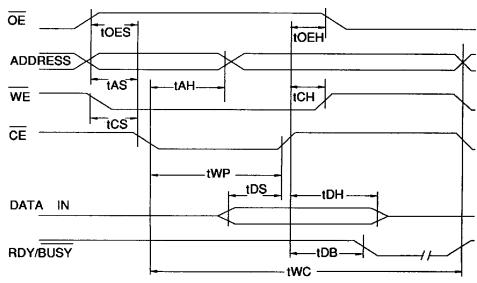
## **A.C. Write Characteristics**

Symbol	Parameter		Min	Тур	Max	Units
tas, toes	Address, OE Set-up Time		10			ns ·
tah	Address Hold Time		50			ns
twp	Write Pulse Width (WE or CE)		100		1000	. ns
tos	Data Set-up Time		50			ns
tDH,tOEH	Data, OE Hold Time		10			ns
tDB	Time to Device Busy				50	ns
twc	Write Cycle Time	AT28C64		0.5	1.0	ms
	Wille Cycle Tille	AT28C64E/F		100	200	μs

# A.C. Write Waveforms- WE Controlled



# A.C. Write Waveforms- CE Controlled



2-96 AT28C64/X

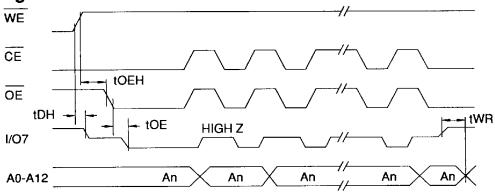
**1**074177 0005043 599 **1** 

# Data Polling Characteristics(1)

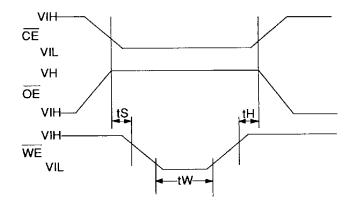
Symbol	Parameter	Min	Тур	Max	Units
tрн	Data Hold Time	10			ns
toeh	OE Hold Time	10			ns
toe	OE to Output Delay			100	ns
twn	Write Recovery Time	0			ns

Note: 1. These parameters are characterized and not 100% tested.

# Data Polling Waveforms



# **Chip Erase Waveforms**



 $t_S = t_H = 1 \mu sec (min.)$   $t_W = 10 msec (min.)$  $V_H = 12.0 V \pm 0.5 V$ 

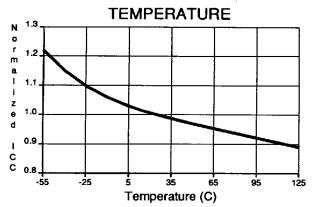


2-97

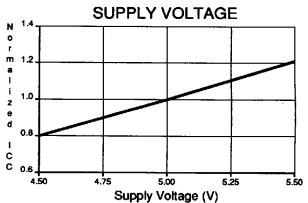
**.** 1074177 0005044 425 **.** 



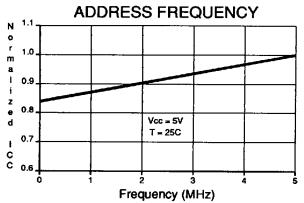
#### NORMALIZED SUPPLY CURRENT vs.



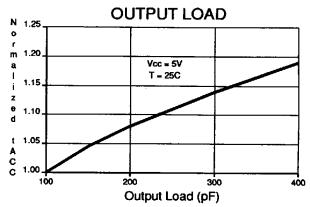
## NORMALIZED SUPPLY CURRENT vs.



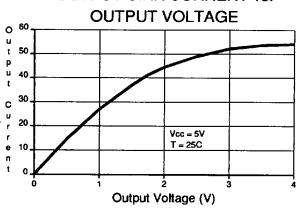
## NORMALIZED SUPPLY CURRENT vs.



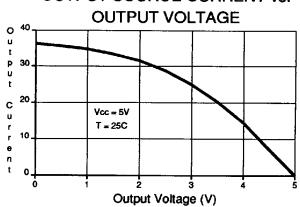
#### NORMALIZED ACCESS TIME vs.



# **OUTPUT SINK CURRENT vs.**



## **OUTPUT SOURCE CURRENT vs.**



2-98 AT28C64/X

**3**074177 0005045 361 **3** 

tacc	lcc	(mA)			0	
(ns)	Active	Standby	Ordering Code	Package	Operation Range	
120	30	0.1	AT28C64(E,F)-12DC AT28C64(E,F)-12JC AT28C64(E,F)-12PC AT28C64(E,F)-12SC	28D6 32J 28P6 28S	Commercial (0°C to 70°C)	
120	120 45		AT28C64(E,F)-12DI AT28C64(E,F)-12JI AT28C64(E,F)-12PI AT28C64(E,F)-12SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)	
			AT28C64(E,F)-12DM/883 AT28C64(E,F)-12FM/883 AT28C64(E,F)-12LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
150	30	0.1	AT28C64(E,F)-15DC AT28C64(E,F)-15JC AT28C64(E,F)-15PC AT28C64(E,F)-15SC AT28C64(E,F)-15TC	28D6 32J 28P6 28S 28T	Commercial (0°C to 70°C)	
150	150 45 0.1		AT28C64(E,F)-15DI AT28C64(E,F)-15JI AT28C64(E,F)-15PI AT28C64(E,F)-15SI AT28C64(E,F)-15TI	28D6 32J 28P6 28S 28T	Industrial (-40°C to 85°C)	
			AT28C64(E,F)-15DM/883 AT28C64(E,F)-15FM/883 AT28C64(E,F)-15LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
200	30	0.1	AT28C64(E,F)-20DC AT28C64(E,F)-20JC AT28C64(E,F)-20PC AT28C64(E,F)-20SC	28D6 32J 28P6 28S	Commercial (0°C to 70°C)	
200	45	0.1	AT28C64(E,F)-20DI AT28C64(E,F)-20JI AT28C64(E,F)-20PI AT28C64(E,F)-20SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)	
			AT28C64(E,F)-20DM/883 AT28C64(E,F)-20FM/883 AT28C64(E,F)-20LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
250	30	0.1	AT28C64(E,F)-25DC AT28C64(E,F)-25JC AT28C64(E,F)-25PC AT28C64(E,F)-25SC AT28C64-W	28D6 32J 28P6 28S DIE	Commercial (0°C to 70°C)	
250	45	0.1	AT28C64(E,F)-25DI AT28C64(E,F)-25JI AT28C64(E,F)-25PI AT28C64(E,F)-25SI	28D6 32J 28P6 28S	Industrial (-40°C to 85°C)	



2-99

🖿 1074177 0005046 2T8 📰



tacc	Icc (mA)		Ondorina Cordo	Deckers	On anti-n Dance (
(ns)	Active	Standby	Ordering Code	Package	Operation Range
250	45	0.1	AT28C64(E,F)-25DM/883 AT28C64(E,F)-25FM/883 AT28C64(E,F)-25LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300 <sup>(1)</sup>	45	0.1	AT28C64(E,F)-30DM/883 AT28C64(E,F)-30FM/883 AT28C64(E,F)-30LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350 <sup>(1)</sup>	45	0.1	AT28C64(E,F)-35DM/883 AT28C64(E,F)-35FM/883 AT28C64(E,F)-35LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
150	45	0.1	5962-87514 17 XX 5962-87514 17 YX	<b>28D6</b> 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	45	0.1	5962-87514 16 XX 5962-87514 16 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
250	45	0.1	5962-87514 15 XX 5962-87514 15 YX 5962-87514 15 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300 <sup>(1)</sup>	45	0.1	5962-87514 14 XX 5962-87514 14 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350 <sup>(1)</sup>	45	0.1	5962-87514 13 XX 5962-87514 13 YX 5962-87514 13 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Notes: 1. Electrical specifications for these speeds are defined in Standardized Military Drawing 5962-87514.

	Package Type					
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)					
28F	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)					
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)					
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)					
28P6	28 Lead, 0.600" Wide, Plastic Dual Inline Package (PDIP)					
285	28 Lead, 0.300" Wide, Plastic Gull Wing, Small Outline (SOIC)					
28T	28 Lead, Plastic Thin Small Outline Package (TSOP)					
W	Die					
Options						
Blank	Standard Device: Endurance = 10K Write Cycles; Write Time = 1 ms					
E	High Endurance Option: Endurance = 100K Write Cycles; Write Time = 200 μs					
F	Fast Write Option: Write Time = 200 μs					

2-100 AT28C64/X =

**-** 1074177 0005047 134 **-**

****	l = -	(mA)				
tacc (ns)	Active	(mA) Standby	Ordering Code	Package	Operation Range	
150	30	0.1	AT28C64X-15DC AT28C64X-15FC AT28C64X-15JC AT28C64X-15PC AT28C64X-15SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)	
150	45	0.1	AT28C64X-15DI AT28C64X-15FI AT28C64X-15JI AT28C64X-15PI AT28C64X-15SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)	
			AT28C64X-15DM/883 AT28C64X-15FM/883 AT28C64X-15LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
200	30	0.1	AT28C64X-20DC AT28C64X-20FC AT28C64X-20JC AT28C64X-20PC AT28C64X-20SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)	
200	45	0.1	AT28C64X-20DI AT28C64X-20FI AT28C64X-20JI AT28C64X-20PI AT28C64X-20SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)	
			AT28C64X-20DM/883 AT28C64X-20FM/883 AT28C64X-20LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
250	30	0.1	AT28C64X-25DC AT28C64X-25FC AT28C64X-25JC AT28C64X-25PC AT28C64X-25SC	28D6 28F 32J 28P6 28S	Commercial (0°C to 70°C)	
250	45	0.1	AT28C64X-25DI AT28C64X-25FI AT28C64X-25JI AT28C64X-25PI AT28C64X-25SI	28D6 28F 32J 28P6 28S	Industrial (-40°C to 85°C)	
			AT28C64X-25DM/883 AT28C64X-25FM/883 AT28C64X-25LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
300	45	0.1	AT28C64X-30DM/883 AT28C64X-30FM/883 AT28C64X-30LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	
350	45	0.1	AT28C64X-35DM/883 AT28C64X-35FM/883 AT28C64X-35LM/883	28D6 28F 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)	



2-101

**I** 1074177 0005048 070 **I** 



tacc (ns)	Icc (mA)		0-1-3-0-1-		
	Active	Standby	Ordering Code	Package	Operation Range
150	45	0.1	5962-87514 22 XX 5962-87514 22 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
200	45	0.1	5962-87514 21 XX 5962-87514 21 YX	28D6 32L	Military/883C Class B, Fully Complian (-55°C to 125°C)
250	45	0.1	5962-87514 20 XX 5962-87514 20 YX 5962-87514 20 ZX	28D6 32L 28F	Military/883C Class B, Fully Compliant (-55°C to 125°C)
300	45	0.1	5962-87514 19 XX 5962-87514 19 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)
350	45	0.1	5962-87514 18 XX 5962-87514 18 YX	28D6 32L	Military/883C Class B, Fully Compliant (-55°C to 125°C)

Package Type				
28D6	28 Lead, 0.600" Wide, Non-Windowed, Ceramic Dual Inline Package (Cerdip)			
28F	28 Lead, Non-Windowed, Ceramic Bottom-Brazed Flat Package (Flatpack)			
32J	32 Lead, Plastic J-Leaded Chip Carrier (PLCC)			
32L	32 Pad, Non-Windowed, Ceramic Leadless Chip Carrier (LCC)			
28P6	28 Lead, 0.600" Wide Plastic Dual Inline Package (PDIP)			
285	28 Lead, 0.300" Wide, Plastic Gull Wing Small Outline (SOIC)			

2-102

AT28C64/X -

■ 1074177 0005049 TO7 ■